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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	25
Program Memory Size	28KB (16K x 14)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.3V ~ 5.5V
Data Converters	A/D 17x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	28-UFQFN Exposed Pad
Supplier Device Package	28-UQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16f1518-e-mv

1.2 Pin Utilization

Five pins are needed for ICSP $^{\text{TM}}$ programming. The pins are listed in Table 1-1 and Table 1-2.

TABLE 1-1: PIN DESCRIPTIONS DURING PROGRAMMING – PIC16(L)F1526 AND PIC16(L)F1527

Pin Name	During Programming				
Pin Name	Function	Pin Type	Pin Description		
RB6	ICSPCLK	I	Clock Input – Schmitt Trigger Input		
RB7	ICSPDAT	I/O	Data Input/Output – Schmitt Trigger Input		
RG5/MCLR/VPP	Program/Verify mode	P ⁽¹⁾	Program Mode Select/Programming Power Supply		
VDD	Vdd	P Power Supply			
Vss	Vss	Р	Ground		

Legend: I = Input, O = Output, P = Power

Note 1: The programming high voltage is internally generated. To activate the Program/Verify mode, high voltage needs to be applied to MCLR input. Since the MCLR is used for a level source, MCLR does not draw any significant current.

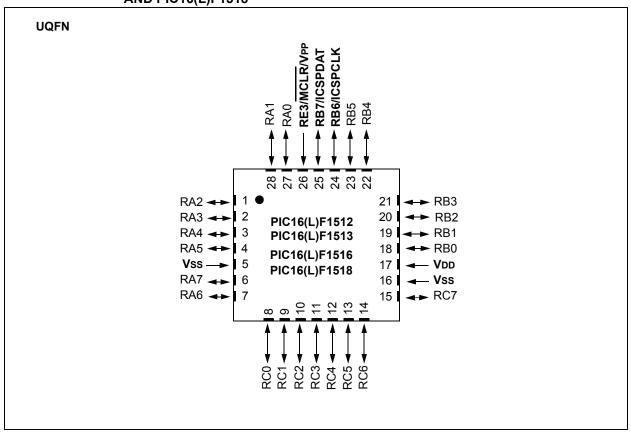
TABLE 1-2: PIN DESCRIPTIONS DURING PROGRAMMING – PIC16(L)F1512, PIC16(L)F1513, PIC16(L)F1516, PIC16(L)F1517, PIC16(L)F1518 and PIC16(L)F1519

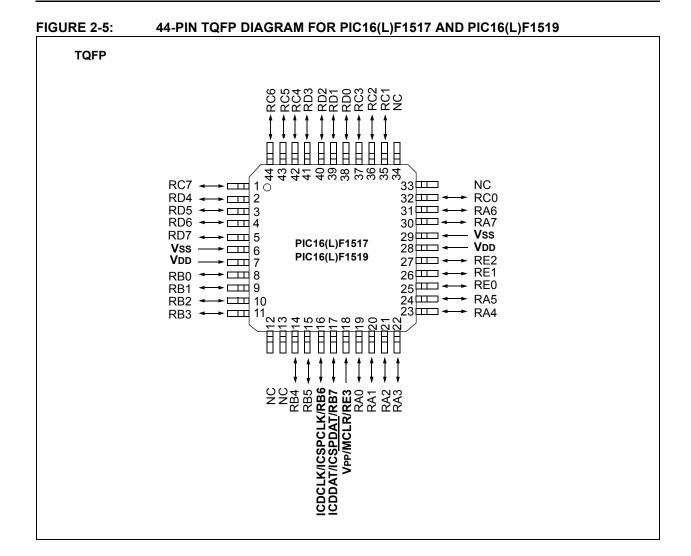
Din Nome	During Programming				
Pin Name	Function	Pin Type	Pin Description		
RB6	ICSPCLK	I	Clock Input – Schmitt Trigger Input		
RB7	ICSPDAT	I/O	Data Input/Output – Schmitt Trigger Input		
RE3/MCLR/VPP	Program/Verify mode	P ⁽¹⁾ Program Mode Select/Programming Power S			
VDD	VDD	Р	Power Supply		
Vss	Vss	Р	Ground		

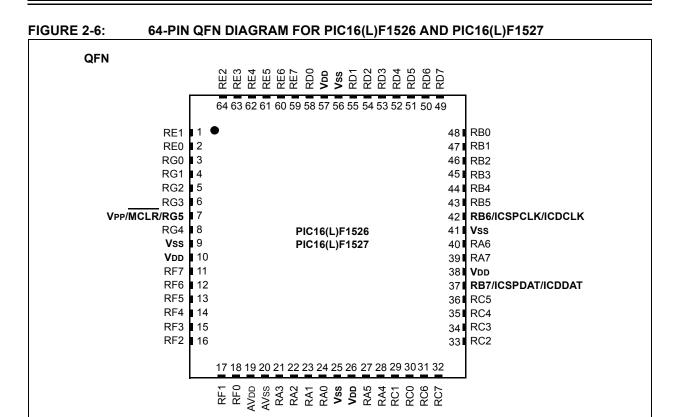
Legend: I = Input, O = Output, P = Power

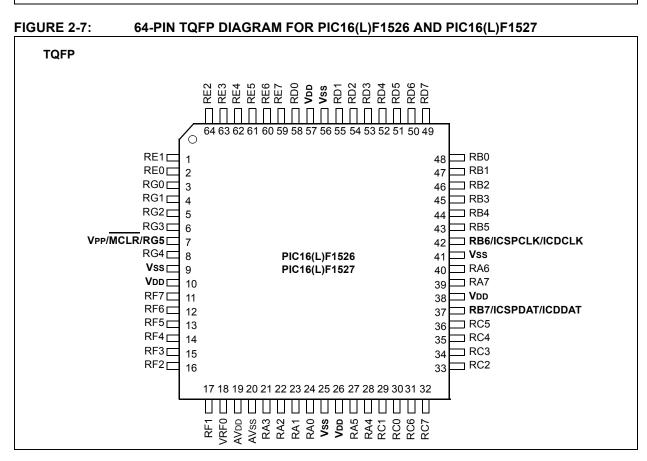
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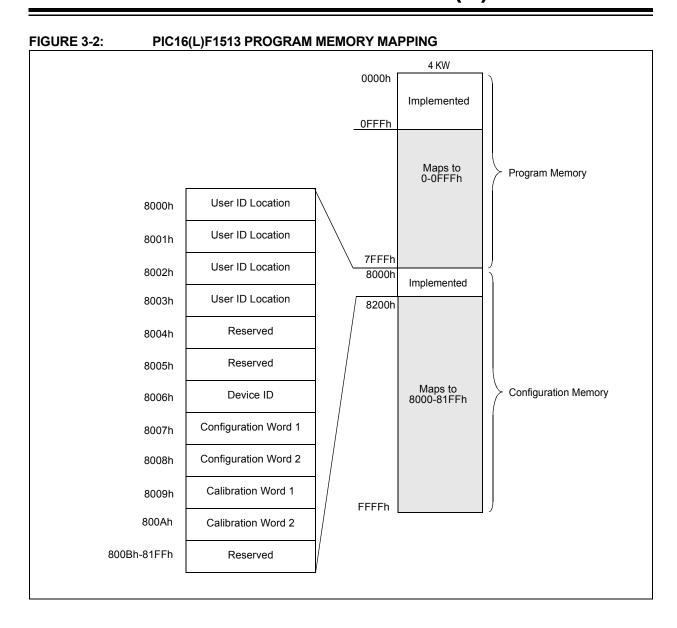
FIGURE 2-2: 28-PIN UQFN DIAGRAM FOR PIC16(L)F1512, PIC16(L)F1513, PIC16(L)F1516 AND PIC16(L)F1518

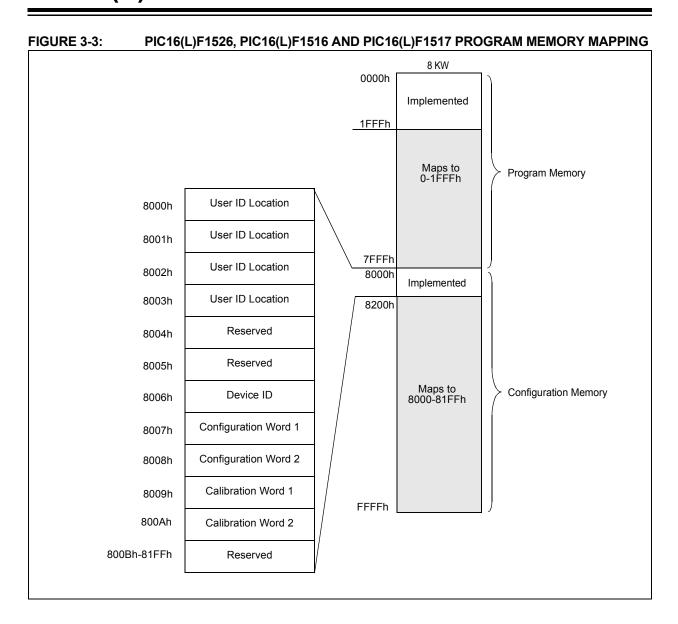












3.1 User ID Location

A user may store identification information (user ID) in four designated locations. The user ID locations are mapped to 8000h-8003h. Each location is 14 bits in length. Code protection has no effect on these memory locations. Each location may be read with code protection enabled or disabled.

Note: MPLAB[®] IDE only displays the 7 Least Significant bits (LSb) of each user ID location, the upper bits are not read. It is recommended that only the 7 LSbs be used if MPLAB IDE is the primary tool used to read these addresses.

3.2 Device ID

The device ID word is located at 8006h. This location is read-only and cannot be erased or modified.

REGISTER 3-1: DEVICE ID: DEVICE ID REGISTER⁽¹⁾

R	R	R	R	R	R		
DEV<8:3>							
bit 13					bit 8		

R	R	R	R	R	R	R	R
	DEV<2:0>				REV<4:0>		
bit 7							bit 0

Legend:	P = Programmable bit	U = Unimplemented bit, read as '0'
R = Readable bit	W = Writable bit	'0' = Bit is cleared
-n = Value at POR	'1' = Bit is set	x = Bit is unknown

bit 13-5 **DEV<8:0>:** Device ID bits

These bits are used to identify the part number.

bit 4-0 **REV<4:0>:** Revision ID bits

These bits are used to identify the revision.

Note 1: This location cannot be written.

REGISTER 3-2: CONFIGURATION WORD 1

R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	U-1	
FCMEN	IESO	CLKOUTEN	BORE	N<1:0>	_	
bit 13					bit	t 8

R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	R/P-1
CP	MCLRE	PWRTE	WDTE<1:0>			FOSC<2:0>	
bit 7							bit 0

Legend:

R = Readable bit P = Programmable bit U = Unimplemented bit, read as '1

'0' = Bit is cleared '1' = Bit is set -n = Value when blank or after Bulk Erase

bit 13 FCMEN: Fail-Safe Clock Monitor Enable bit

1 = Fail-Safe Clock Monitor is enabled

0 = Fail-Safe Clock Monitor is disabled

bit 12 IESO: Internal External Switchover bit

1 = Internal/External Switchover mode is enabled 0 = Internal/External Switchover mode is disabled

bit 11 CLKOUTEN: Clock Out Enable bit

1 = CLKOUT function is disabled. I/O or oscillator function on CLKOUT pin.

0 = CLKOUT function is enabled on CLKOUT pin

bit 10-9 **BOREN<1:0>:** Brown-out Reset Enable bits⁽¹⁾

11 = BOR enabled

10 = BOR enabled during operation and disabled in Sleep

01 = BOR controlled by SBOREN bit of the PCON register

00 = BOR disabled

bit 8 Unimplemented: Read as '1'

bit 7 **CP**: Code Protection bit⁽²⁾

1 = Program memory code protection is disabled

0 = Program memory code protection is enabled

bit 6 MCLRE: MCLR/VPP Pin Function Select bit

If LVP bit = 1:

This bit is ignored.

If LVP bit = 0:

1 = \overline{MCLR}/VPP pin function is \overline{MCLR} ; Weak pull-up enabled.

0 = MCLR/VPP pin function is digital input; MCLR internally disabled; Weak pull-up under control of WPUA register.

bit 5 **PWRTE**: Power-up Timer Enable bit⁽¹⁾

1 = PWRT disabled

0 = PWRT enabled

bit 4-3 WDTE<1:0>: Watchdog Timer Enable bit

11 = WDT enabled

10 = WDT enabled while running and disabled in Sleep

01 = WDT controlled by the SWDTEN bit in the WDTCON register

00 = WDT disabled

bit 2-0 FOSC<2:0>: Oscillator Selection bits

111 = ECH: External Clock, High-Power mode: on CLKIN pin

110 = ECM: External Clock, Medium-Power mode: on CLKIN pin

101 = ECL: External Clock, Low-Power mode: on CLKIN pin

100 = INTOSC oscillator: I/O function on OSC1 pin

011 = EXTRC oscillator: RC function on OSC1 pin

010 = HS oscillator: High-speed crystal/resonator on OSC2 pin and OSC1 pin

001 = XT oscillator: Crystal/resonator on OSC2 pin and OSC1 pin

000 = LP oscillator: Low-power crystal on OSC2 pin and OSC1 pin

Note 1: Enabling Brown-out Reset does not automatically enable Power-up Timer.

2: The entire program memory will be erased when the code protection is turned off.

REGISTER 3-3: CONFIGURATION WORD 2

R/P-1	R/P-1	R/P-1	R/P-1	R/P-1	U-1
LVP	DEBUG	LPBOR	BORV	STVREN	_
bit 13					bit 8

U-1	U-1	U-1	R/P-1	U-1	U-1	R/P-1	R/P-1
_	_	_	VCAPEN ⁽²⁾	_	_	WRT<	:1:0>
bit 7							bit 0

Legend:		
R = Readable bit	P = Programmable bit	U = Unimplemented bit, read as '1
'0' = Bit is cleared	'1' = Bit is set	-n = Value when blank or after Bulk Erase

bit 13 LVP: Low-Voltage Programming Enable bit⁽¹⁾

1 = Low-voltage programming enabled

0 = HV on \overline{MCLR}/VPP must be used for programming

bit 12 **DEBUG:** In-Circuit Debugger Mode bit

 ${\tt 1}$ = In-Circuit Debugger disabled, ICSPCLK and ICSPDAT are general purpose I/O pins

0 = In-Circuit Debugger enabled, ICSPCLK and ICSPDAT are dedicated to the debugger

bit 11 LPBOR: Low-Power BOR

1 = Low-Power BOR is disabled

0 = Low-Power BOR is enabled

bit 10 BORV: Brown-out Reset Voltage Selection bit

1 = Brown-out Reset voltage (VBOR), low trip point selected

0 = Brown-out Reset voltage (VBOR), high trip point selected

bit 9 STVREN: Stack Overflow/Underflow Reset Enable bit

1 = Stack Overflow or Underflow will cause a Reset

0 = Stack Overflow or Underflow will not cause a Reset

bit 8-5 **Unimplemented:** Read as '1'

bit 4

VCAPEN: Voltage Regulator Capacitor Enable bits⁽¹⁾

0 = VCAP functionality is enabled on VCAP pin

1 = All VCAP pin functions are disabled

bit 3-2 Unimplemented: Read as '1'

bit 1-0 WRT<1:0>: Flash Memory Self-Write Protection bits

2 kW Flash memory (PIC16(L)F1512):

11 = Write protection off

10 = 000h to 1FFh write-protected, 200h to 7FFh may be modified by PMCON control

01 = 000h to FFFh write-protected, 400h to 7FFh may be modified by PMCON control

00 = 000h to 7FFh write-protected, no addresses may be modified by PMCON control

4 kW Flash memory (PIC16(L)F1513):

11 = Write protection off

10 = 000h to 1FFh write-protected, 200h to FFFh may be modified by PMCON control

01 = 000h to 7FFh write-protected, 800h to FFFh may be modified by PMCON control

00 = 000h to FFFh write-protected, no addresses may be modified by PMCON control

8 kW Flash memory (PIC16F/LF1516/1517/1526):

11 = Write protection off

10 = 000h to 1FFh write-protected, 200h to 1FFFh may be modified by PMCON control

01 = 000h to FFFh write-protected, 1000h to 1FFFh may be modified by PMCON control

00 = 000h to 1FFFh write-protected, no addresses may be modified by PMCON control

16 kW Flash memory (PIC16F/LF1518/1519/1527):

11 = Write protection off

10 = 000h to 1FFh write-protected, 200h to 3FFFh may be modified by PMCON control

01 = 000h to 1FFFh write-protected, 2000h to 3FFFh may be modified by PMCON control

00 = 000h to 3FFFh write-protected, no addresses may be modified by PMCON control

Note 1: The LVP bit cannot be programmed to '0' when Programming mode is entered via LVP.

Applies to PIC16F151X/152X devices only. On PIC16LF151X/152X, the VCAPEN bit is unimplemented.

4.0 PROGRAM/VERIFY MODE

In Program/Verify mode, the program memory and the configuration memory can be accessed and programmed in serial fashion. ICSPDAT and ICSPCLK are used for the data and the clock, respectively. All commands and data words are transmitted LSb first. Data changes on the rising edge of the ICSPCLK and latched on the falling edge. In Program/Verify mode both the ICSPDAT and ICSPCLK are Schmitt Trigger inputs. The sequence that enters the device into Program/Verify mode places all other logic into the Reset state. Upon entering Program/Verify mode, all I/Os are automatically configured as high-impedance inputs and the address is cleared.

4.1 High-Voltage Program/Verify Mode Entry and Exit

There are two different methods of entering Program/ Verify mode via high-voltage:

- VPP First entry mode
- VDD First entry mode

4.1.1 VPP – FIRST ENTRY MODE

To enter Program/Verify mode via the VPP-first method the following sequence must be followed:

- 1. Hold ICSPCLK and ICSPDAT low. All other pins should be unpowered.
- 2. Raise the voltage on MCLR from 0V to VIHH.
- 3. Raise the voltage on VDD FROM 0V to the desired operating voltage.

The VPP-first entry prevents the device from executing code prior to entering Program/Verify mode. For example, when Configuration Word 1 has MCLR disabled (MCLRE = 0), the power-up time is disabled (PWRTE = 0), the internal oscillator is selected (Fosc = 100), and ICSPCLK and ICSPDAT pins are driven by the user application, the device will execute code. Since this may prevent entry, VPP-first entry mode is strongly recommended. See the timing diagram in Figure 8-2.

4.1.2 VDD – FIRST ENTRY MODE

To enter Program/Verify mode via the VDD-first method the following sequence must be followed:

- Hold ICSPCLK and ICSPDAT low.
- Raise the voltage on VDD from 0V to the desired operating voltage.
- Raise the voltage on MCLR from VDD or below to VIHH.

The VDD-first method is useful when programming the device when VDD is already applied, for it is not necessary to disconnect VDD to enter Program/Verify mode. See the timing diagram in Figure 8-1.

4.1.3 PROGRAM/VERIFY MODE EXIT

To exit Program/Verify mode take MCLR to VDD or lower (VIL). See Figures 8-3 and 8-4.

4.2 Low-Voltage Programming (LVP) Mode

The Low-Voltage Programming mode allows the PIC16(L)F151X/152X devices to be programmed using VDD only, without high voltage. When the LVP bit of Configuration Word 2 register is set to '1', the low-voltage ICSP programming entry is enabled. To disable the Low-Voltage ICSP mode, the LVP bit must be programmed to '0'. This can only be done while in the High-Voltage Entry mode.

Entry into the Low-Voltage ICSP Program/Verify modes requires the following steps:

- 1. MCLR is brought to VIL.
- A 32-bit key sequence is presented on ICSPDAT, while clocking ICSPCLK.

The key sequence is a specific 32-bit pattern, '0100 1101 0100 0011 0100 1000 0101 0000' (more easily remembered as MCHP in ASCII). The device will enter Program/Verify mode only if the sequence is valid. The Least Significant bit of the Least Significant nibble must be shifted in first.

Once the key sequence is complete, \overline{MCLR} must be held at VIL for as long as Program/Verify mode is to be maintained.

For low-voltage programming timing, see Figure 8-8 and Figure 8-9.

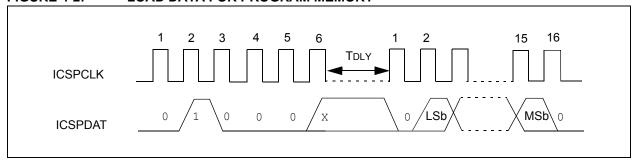
Exiting Program/Verify mode is done by no longer driving MCLR to VIL. See Figure 8-8 and Figure 8-9.

Note: To enter LVP mode, the LSB of the Least Significant nibble must be shifted in first. This differs from entering the key sequence on other parts.

4.3.2 LOAD DATA FOR PROGRAM MEMORY

The Load Data for Program Memory command is used to load one 14-bit word into the data latches. The word programs into program memory after the Begin Internally Timed Programming or Begin Externally Timed Programming command is issued (see Figure 4-2).

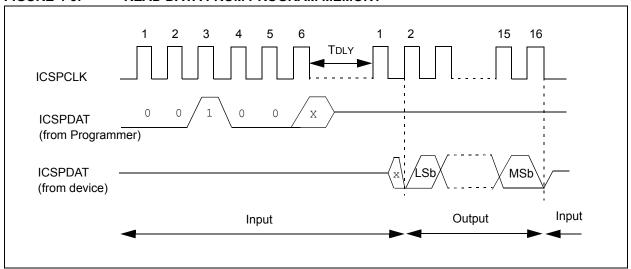
FIGURE 4-2: LOAD DATA FOR PROGRAM MEMORY



4.3.3 READ DATA FROM PROGRAM MEMORY

The Read Data from Program Memory command will transmit data bits out of the program memory map currently accessed, starting with the second rising edge of the clock input. The ICSPDAT pin will go into Output mode on the first falling clock edge, and it will revert to Input mode (high-impedance) after the 16th falling edge of the clock. If the program memory is code-protected (\overline{CP}) , the data will be read as zeros (see Figure 4-3).

FIGURE 4-3: READ DATA FROM PROGRAM MEMORY



4.3.10 **ROW ERASE PROGRAM MEMORY**

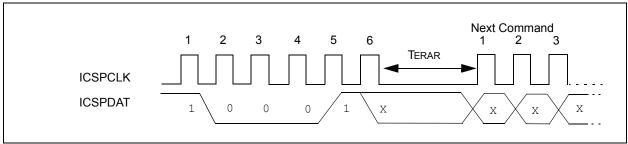
The Row Erase Program Memory command will erase an individual row. Refer to Table 4-2 for row sizes of specific devices and the PC bits used to address them. If the program memory is code-protected the Row Erase Program Memory command will be ignored. When the address is 8000h-8008h the Row Erase Program Memory command will only erase the user ID locations regardless of the setting of the CP Configuration bit.

After receiving the Row Erase Program Memory command the erase will not complete until the time interval, TERAR, has expired.

TABLE 4-2: PROGRAMMING ROW SIZE AND LATCHES

Devices	PC	Row Size	Number of Latches
PIC16(L)F151X/152X	<15:5>	32	32





5.0 PROGRAMMING ALGORITHMS

The devices use internal latches to temporarily store the 14-bit words used for programming. Refer to Table 4-2 for specific latch information. The data latches allow the user to write the program words with a single Begin Externally Timed Programming or Begin Internally Timed Programming command. The Load Program Data or the Load Configuration command is used to load a single data latch. The data latch will hold the data until the Begin Externally Timed Programming or Begin Internally Timed Programming command is given.

The data latches are aligned with the LSbs of the address. The PC's address at the time the Begin Externally Timed Programming or Begin Internally Timed Programming command is given will determine which location(s) in memory are written. Writes cannot cross the physical boundary. For example, with the PIC16F1527, attempting to write from address 0002h-0009h will result in data being written to 0008h-000Fh.

If more than the maximum number of data latches are written without a Begin Externally Timed Programming or Begin Internally Timed Programming command, the data in the data latches will be overwritten. The following figures show the recommended flowcharts for programming.

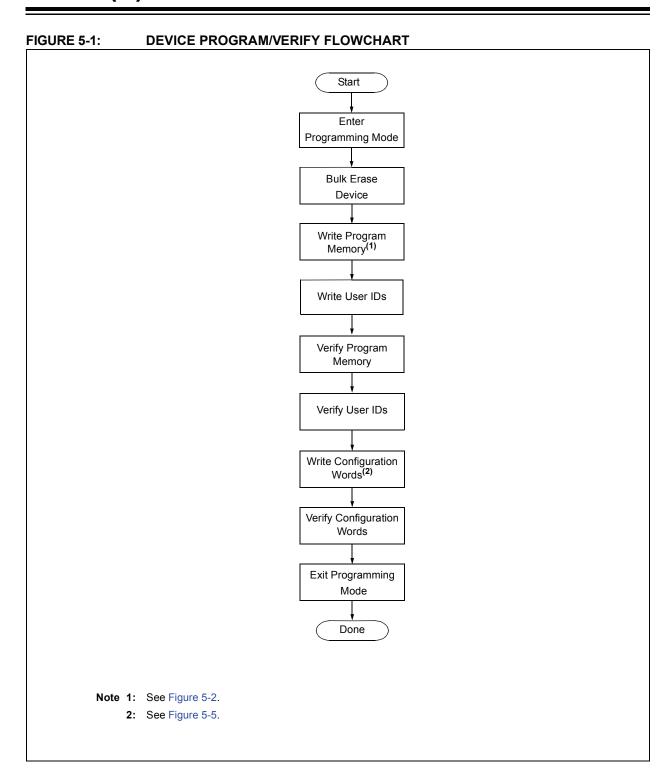
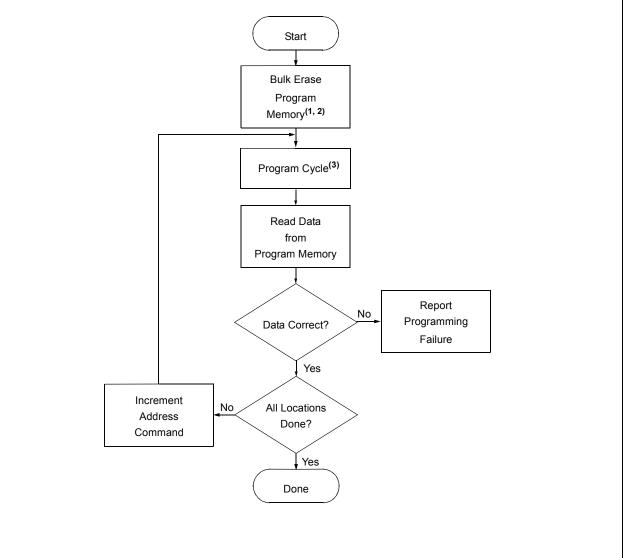
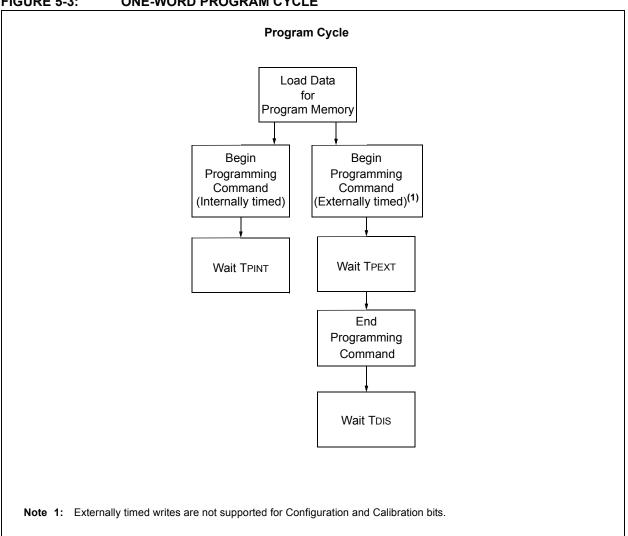


FIGURE 5-2: PROGRAM MEMORY FLOWCHART



- Note 1: This step is optional if device has already been erased or has not been previously programmed.
 - 2: If the device is code-protected or must be completely erased, then Bulk Erase device per Figure 5-6.
 - **3:** See Figure 5-3 or Figure 5-4.

FIGURE 5-3: **ONE-WORD PROGRAM CYCLE**



EXAMPLE 7-1: CHECKSUM COMPUTED WITH PROGRAM CODE PROTECTION DISABLED PIC16F1527, BLANK DEVICE

PIC16F1527 Sum of Memory addresses 0000h-3FFFh⁽¹⁾ C000h
Configuration Word 1⁽²⁾ 3FFFh
Configuration Word 1 mask⁽³⁾ 3EFFh
Configuration Word 2⁽²⁾ 3FFFh
Configuration Word 2 mask⁽³⁾ 3E13h

Checksum = C000h + (3FFFh and 3EFFh) + (3FFFh and 3E13h)

= C000h + 3EFFh + 3E13h

= 3D12h

Note 1: Sum of memory addresses = (Total number of program memory address locations) x (3FFFh) = C000h, truncated to 16 bits.

2: Configuration Word 1 and 2 = all bits are '1'; thus, code-protect is disabled.

3: Configuration Word 1 and 2 Mask = all bits are set to '1', except for unimplemented bits that are '0'.

EXAMPLE 7-2: CHECKSUM COMPUTED WITH PROGRAM CODE PROTECTION DISABLED PIC16LF1527, 00AAh AT FIRST AND LAST ADDRESS

PIC16LF1527 Sum of Memory addresses 0000h-3FFFh⁽¹⁾

Configuration Word 1⁽²⁾

Configuration Word 1 mask⁽³⁾

Configuration Word 2⁽²⁾

Configuration Word 2 mask⁽⁴⁾

3E93h

Checksum = 4156h + (3FFFh and 3EFFh) + (3FFFh and 3E03h)

= 4156h + 3EFFh + 3E03h

= BE58h

Note 1: Total number of Program memory address locations: 3FFFh + 1 = 4000h. Then, 4000h - 2 = 3FFEh. Thus, [(3FFEh x 3FFFh) + (2 x 00AAh)] = 4156h, truncated to 16 bits.

- 2: Configuration Word 1 and 2 = all bits are '1'; thus, code-protect is disabled.
- **3:** Configuration Word 1 Mask = all Configuration Word bits are set to '1', except for unimplemented bits that are '0'.
- **4:** On the PIC16LF1527 device, the VCAPEN bit is not implemented in Configuration Word 2; Thus, all unimplemented bits are '0'.

8.0 ELECTRICAL SPECIFICATIONS

Refer to device specific data sheet for absolute maximum ratings.

TABLE 8-1: AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY MODE

AC/DC CHARACTERISTICS			Standard Operating Conditions Production tested at 25°C				
Sym.	Characteristics		Min.	Тур.	Max.	Units	Conditions/Comments
		Supply Volt	ages and C	urrents			
VDD	Supply Voltage	PIC16F151X PIC16F152X	2.3	_	5.5	V	
	(VDDMIN, VDDMAX)	PIC16LF151X PIC16LF152X	1.8	_	3.6	V	
VPEW	Read/Write and Row Erase operations		VDDMIN	_	VDDMAX	V	
VPBE	Bulk Erase operations		2.7	_	VDDMAX	V	
Iddi	Current on VDD, Idle		_	_	1.0	mA	
IDDP	Current on VDD, Programming		_	_	3.0	mA	
	VPP						
IPP	Current on MCLR/VPP		_	_	600	μΑ	
VIHH	High voltage on MCLR/VPP for Program/Verify mode entry		8.0	_	9.0	V	
TVHHR	HHR MCLR rise time (VIL to VIHH) for Program/Verify mode entry		_	_	1.0	μS	
	I/O pins						
VIH	(ICSPCLK, ICSPDAT, MCLR/VPP) input high level		0.8 VDD	_	_	V	
VIL	(ICSPCLK, ICSPDAT, MCLR/VPP) input low level		_	_	0.2 VDD	V	
Vон	ICSPDAT output high level		VDD-0.7 VDD-0.7 VDD-0.7	_	_	V	IOH = 3.5 mA, VDD = 5V IOH = 3 mA, VDD = 3.3V IOH = 2 mA, VDD = 1.8V
Vol	ICSPDAT output low level		_	_	Vss+0.6 Vss+0.6 Vss+0.6	V	IOH = 8 mA, VDD = 5V IOH = 6 mA, VDD = 3.3V IOH = 3 mA, VDD = 1.8V
		Programming	Mode Entry	and Exi	t	<u>l</u>	<u> </u>
TENTS	Programing mode entry setup time: ICSPCLK, ICSPDAT setup time before VDD or MCLR↑		100	_	_	ns	
TENTH	Programing mode entry hold time: ICSPCLK, ICSPDAT hold time after VDD or MCLR↑		250	_	_	μS	
		Serial F	Program/Vei	rify			
TCKL	Clock Limb Pulse Width		100		_	ns	
ТСКН	Clock High Pulse Width		100	_		ns	
TDS	Data in setup time before clock↓ Data in hold time after clock↓		100 100			ns	
TDH	Clock↑ to data out valid (during a		100	_	_	ns	
Tco	Read Data command)		0	_	80	ns	
TLZD	Clock↓ to data low-impedance (during a Read Data command)		0	_	80	ns	
THZD	Clock↓ to data high-impedance (during a Read Data command)		0	_	80	ns	
TDLY	Data input not driven to next clock input (delay required between command/data or command/ command)		1.0	_	_	μS	
TERAB	Bulk Erase cycle time		_	_	5	ms	
TERAR	Row Erase cycle time		—	_	2.5	ms	

Note 1: Externally timed writes are not supported for Configuration and Calibration bits.

FIGURE 8-8: LVP ENTRY (POWERED)

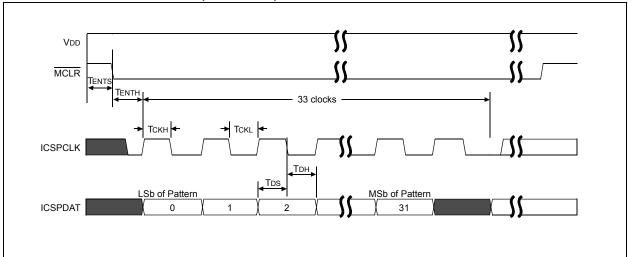
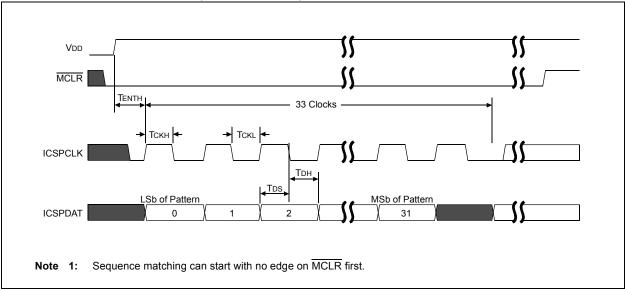


FIGURE 8-9: LVP ENTRY (POWERING UP)



APPENDIX A: REVISION HISTORY

Revision A (08/2010)

Original release of this document.

Revision B (09/2011)

Added PIC16(L)F1512/1513 devices; Added new Figures 3-1 and 3-2; Updated Registers 3-1, 3-2 and 3-3 to new format; Updated Register 3-3 to add 2 kW and 4 kW Flash memory; Added Notes to Examples 7-1 to 7-4; Updated Table 8-1; Other minor corrections.